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BLV11

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

BLV11 is Designed for Class C, 12.5 Volt operation in FM Amplifier Applications up to 250 MHz.

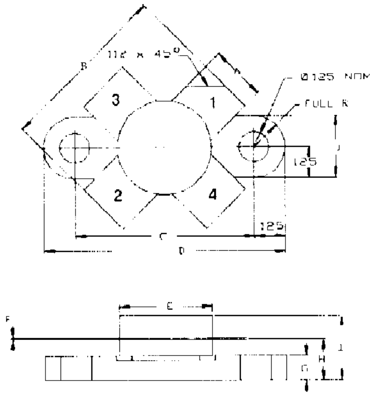
FEATURES INCLUDE:

- P_G = 9.0 dB Typical at 175 MHz
- Emitter Ballasting
- ***Omnigold***™ Metalization System

MAXIMUM RATINGS

I_C	3.0 A
V_{CE}	18 V
V_{CB}	36 V
P_{DISS}	37 W @ T_C = 25 °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	4.6 °C/W

PACKAGE STYLE .375 4L FLG



	MINIMUM Inches/mm	MAXIMUM Inches/mm
A	.220/5,59	.230/5,84
B	785/19,94	
C	720/18,29	.730/18,54
D	970/24,64	.980/24,89
E		.385/9,78
F	.004/0,10	.006/0,15
G	.085/2,16	.105/2,67
H	.160/4,06	.180/4,57
I		.280/7,11
[illegible]	.240/6,10	.255/6,48

1 = Collector 2 = Base
3 & 4 = Emitter

CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CBO}	I_C = 20 mA	36			V
BV_{CES}	I_C = 50 mA	36			V
BV_{CEO}	I_C = 50 mA	18			V
BV_{EBO}	I_E = 5.0 mA	4.0			V
I_{CBO}	V_{CB} = 15 V			2.0	mA
h_{FE}	V_{CE} = 5.0 V I_C = 250 mA	5.0	50		---
C_{ob}	V_{CB} = 12.5 V f = 1.0 MHz		45		pF
P_G η_C	V_{CE} = 13.5 V P_{OUT} = 15 W f = 175 MHz	8.0 60	9.0 65		dB %